



P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} MAX	I _D Τ _A = +25°C
-30V	45mΩ @ V _{GS} = -10V	-4.3A
-30 V	65mΩ @ V _{GS} = -4.5V	-3.3A

Description

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- General Purpose Interfacing Switch
- Power Management Functions
- Analog Switch

Features

- Low Gate Threshold Voltage
- Low On-Resistance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

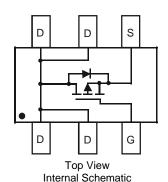
Mechanical Data

- Case: SOT26
- Case Material Molded Plastic, "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.016 grams (Approximate)





Top View



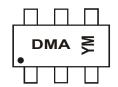
Ordering Information (Note 5)

Part Number	Qualification	Case	Packaging
DMP3056LDM-7	Commercial	SOT26	3000/Tape & Reel
DMP3056LDMQ-7	Automotive	SOT26	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/product_compliance_definitions.html.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



DMA = Product Type Marking Code YM = Date Code Marking Y = Year (ex: V = 2008)

M = Month (ex: 9 = September)

Date Code Key

Year	2008		~	2016		2017	2018	1	2019	2020)	2021
Code	V		~	D		Е	F		G	Н		
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	g Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

DMP3056LDM
Document number: DS31449 Rev. 12 - 2



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V _{DSS}	-30	V	
Gate-Source Voltage		V_{GSS}	±20	V	
Continuous Drain Current (Note 7) V _{GS} = -10V	Steady State	$T_A = +25^{\circ}C$	I _D	-4.3	А
Continuous Diam Current (Note 7) VGS = 10V	t < 10s	T _A = +25°C	I _D	-5.8	Α
Maximum Continuous Body Diode Forward Curre	ent (Note 7)	I _S	-2.3	А	
Pulsed Drain Current (10μs Pulse, Duty Cycle =	1%)	I_{DM}	-13	Α	

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$	P_{D}	1.25	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	100	°C/W
Total Power Dissipation (Note 7)	T _A = +25°C	P _D	1.5	W
Thermal Resistance, Junction to Ambient (Note 7) Steady State		$R_{\theta JA}$	86	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	15.6	C/VV	
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

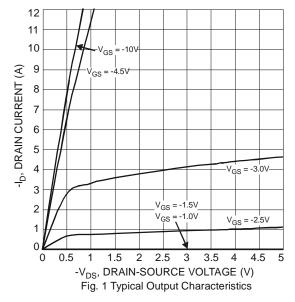
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

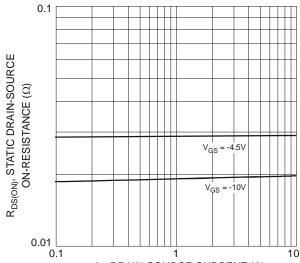
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
STATIC PARAMETERS (Note 8)	Syllibol	IVIIII	тур	IVIAA	Oilit	rest condition	
Drain-Source Breakdown Voltage	BV _{DSS}	-30	_	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C		_	_	-1	μА	$V_{GS} = 0V, V_{DS} = -30V$	
Gate-Body Leakage Current	I _{GSS}	_	_	±100 ±800	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$ $V_{GS} = \pm 25V, V_{DS} = 0V$	
Gate Threshold Voltage	V _{GS(TH)}	-1.0	_	-2.1	V	$V_{GS} = V_{DS}, I_D = -250 \mu A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_		45 65	mΩ	$V_{GS} = -10V, I_D = -5A$ $V_{GS} = -4.5V, I_D = -4.2A$	
Forward Transconductance	g FS	_	8	_	S	$V_{DS} = -10V, I_D = -4.3A$	
Diode Forward Voltage	V _{SD}	_	_	-1.2	V	$V_{GS} = 0V, I_{S} = -1.7A$	
DYNAMIC PARAMETERS (Note 9)							
Input Capacitance	Ciss	_	948	_	pF	.,	
Output Capacitance Reverse Transfer Capacitance		_	105	_	pF	$V_{GS} = 0V, V_{DS} = -25V,$ - f = 1.0MHz	
		_	100	_	pF	1 = 1.000112	
SWITCHING CHARACTERISTICS (Note 9)							
Total Gate Charge		_	10.1	_	nC	$V_{DS} = -15V$, $V_{GS} = -4.5V$, $I_{D} = -6A$	
	Q_{g}	_	21.1	_		V _{DS} = -15V, V _{GS} = -10V.	
Gate-Source Charge	Q_{gs}	_	2.8	_	nC	$V_{DS} = -15V$, $V_{GS} = -10V$, $I_{D} = -6A$	
Gate-Drain Charge		_	3.2	_		ID = -6A	
Gate Resistance	R_g	_	13.15	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Turn-On Delay Time Rise Time		_	10.2	_			
		_	6.6			$V_{DS} = -15V, V_{GS} = -10V,$	
Turn-Off Delay Time			50.1	_	ns	$I_D = -1A$, $R_g = 6.0\Omega$	
Fall Time	t _F	_	22.3	_			

Notes:

- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to product testing.







-I_D, DRAIN-SOURCE CURRENT (A)
Fig. 3 On-Resistance vs. Drain Current & Gate Voltage

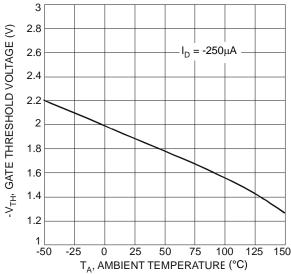
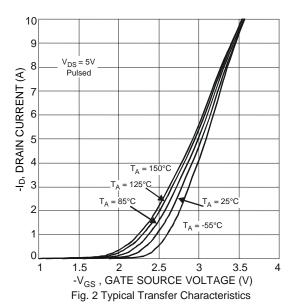


Fig. 5 Gate Threshold Variation vs. Ambient Temperature



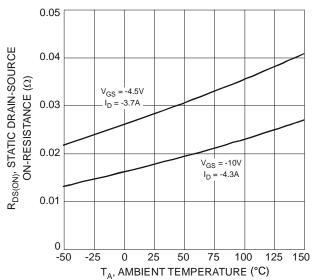
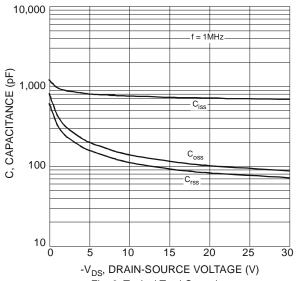


Fig. 4 Static Drain-Source On-Resistance vs. Ambient Temperature





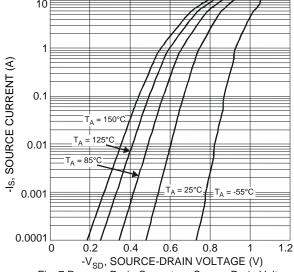
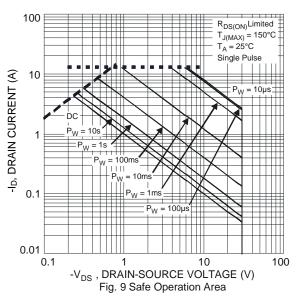


Fig. 7 Reverse Drain Current vs. Source-Drain Voltage



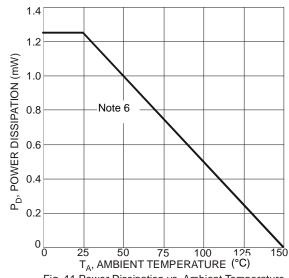


Fig. 11 Power Dissipation vs. Ambient Temperature

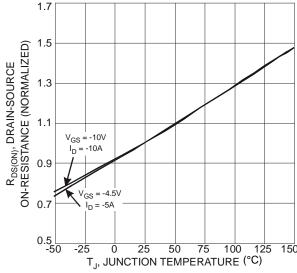
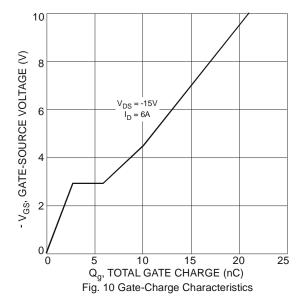
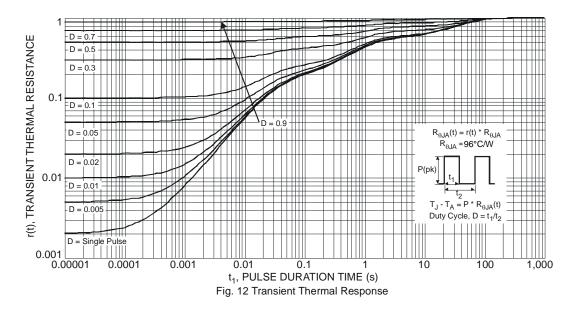


Fig. 8 On-Resistance Variation with Temperature



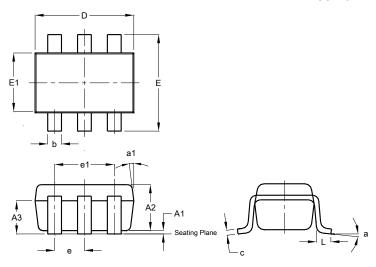




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT26

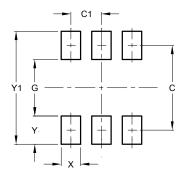


SOT26							
Dim	Min	Max	Тур				
A1	0.013	0.10	0.05				
A2	1.00	1.30	1.10				
A3	0.70	0.80	0.75				
b	0.35	0.50	0.38				
С	0.10	0.20	0.15				
D	2.90	3.10	3.00				
е	-	-	0.95				
e1	-	-	1.90				
Е	2.70	3.00	2.80				
E1	1.50	1.70	1.60				
L	0.35	0.55	0.40				
а	-	-	8°				
a1	-	-	7°				
All	All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT26



Dimensions	Value (in mm)
С	2.40
C1	0.95
G	1.60
Х	0.55
Υ	0.80
Y1	3.20



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